

# **S-UM5587EF**

# 16-CHANNEL PROGRAMMABLE 3-LEVEL HIGH-VOLTAGE ULTRASOUND TRANSMIT BEAMFORMER

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S-UM5587EF is a 16-channel programmable 3-level high-voltage ultrasound transmit beam-former.

The S-UM5587EF comprises control logic, waveform memory, delay calculator, level translators, gate drive buffers with floating voltage regulators, high-voltage, high-current MOSFETs, and active T/R switches.

#### ■ Functions

• 16-channel programmable 3-level transmit beam-former with active T/R-switch

#### ■ Features

- 0 to ±100V output voltage
- ±1A source and sink current with 2-mode current control for the high-voltage pulses
- ±0.5A source and sink peak current for active ground clamp
- 250Ω active ground clamp without blocking diode for anti-leakage
- 20MHz output frequency at ±60V output, 80pF load
- Symmetrical positive and negative pulse waveforms for low 2nd order harmonic distortion
- 1.8V to 3.3V LVCMOS logic interface
- Waveform memory and registers with 100MHz Write /50MHz Read SPI
- 0.2µs to 41µs common delay time range from TRIG signal
- 0 to 2.55µs channel-to-channel delay time range
- 5ns channel-to-channel delay time resolution with dual-edge 100MHz LVDS/LVCMOS clock
- Minimum 10ns pulse width with 5ns time resolution with dual-edge 100MHz LVDS/LVCMOS clock
- 28Ω active T/R switch
- · Noise-cut diodes at each high-voltage output
- High-voltage clamp diodes between each high-voltage output and power rails
- · Automatic thermal protection with indicator
- Power-up/down reset function for free power sequencing and for fail-safe in abrupt power drop
- Latch-up free, low crosstalk between channels by SOI CMOS technology
- QFN-68(1010)B: 68-lead 10x10mm QFN package (RoHS compliant)

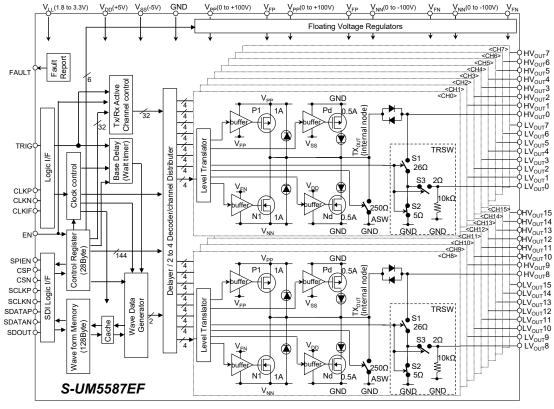


Figure 1 Block Diagram

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# ■ Absolute Maximum Ratings

T<sub>A</sub> = 25°C unless otherwise specified.

Table 1 Absolute Maximum Ratings

No.	Items	Symbol	Value	Units	Condition
1	Logic supply voltage	VLL	-0.4 to +7	V	
2	Positive supply voltage	$V_{DD}$	-0.4 to +7	V	
3	Negative supply voltage	Vss	-7 to +0.4	V	
4	Positive high-voltage supplies	$V_{PP}$	-0.5 to +105	V	
5	Negative high-voltage supplies	V <sub>NN</sub>	-105 to +0.5	V	
6	High-voltage outputs $(x = 0 \text{ to } 15)$	HV <sub>оит</sub> х	-105 to +105	V	
7	Low-voltage outputs (x = 0 to 15)	LV <sub>OUT</sub> X	-1 to +1	V	
8	Logic output voltage	SDOUT, FAULT	-0.4 to +7	V	
9	Logic input voltages	EN, CLKIF, CLKP, CLKN, TRIG, SPIEN, CSP, CSN, SCLKP, SCLKN, SDATAP, SDATAN	-0.4 to +7	V	
10	Operating junction temperature	$T_Jop$	-20 to +125	°C	
11	Storage temperature	T <sub>STG</sub>	-55 to +150	°C	
12	Maximum power dissipation	P <sub>Dmax</sub>	4	W	

Remark Stresses beyond the absolute maximum ratings may cause permanent damage to the product.

# ■ Operating Supply Voltages and Logic Inputs

# 1. Operating supply voltage and temperature

Table 2 Operating Supply Voltage and Temperature

No.	Items	Symbol	Min.	Тур.	Max.	Units	Condition
1	Logic supply voltage	$V_{LL}$	1.71	1.8 to 3.3	3.6	<b>V</b>	
2	Positive supply voltage	$V_{DD}$	4.75	5	5.25	V	
3	Negative supply voltage	Vss	-5.25	-5	-4.75	V	
4	Positive high-voltage supplies	$V_{PP}$	0	-	100	V	
5	Negative high-voltage supplies	$V_{NN}$	-100	-	0	V	
6	IC substrate voltage *1	V <sub>SUB</sub>	-	0	-	V	
7	V <sub>PP</sub> _, V <sub>NN</sub> _ slew rate	SRMAX	-	-	25	V/ms	
8	Operating free-air temperature	Ta	0	-	75	°C	

<sup>\*1.</sup> The package exposed pad internally connected to the chip substrate must be soldered to the ground.

# 2. Logic inputs and outputs

# 2.1 LVDS differential logic inputs

Table 3 CLKP/CLKN, CSP/CSN, SCLKP/SCLKN, SDATAP/SDATAN

No.	Items	Symbol	Min.	Тур.	Max.	Units	Condition
1	High-level input voltage	VIH	1.265	_	_	V	VIHCMR(Typ) + VDIFF(Min)/2
2	Low-level input voltage	VIL	_	_	1.135	V	VIHCMR(Typ) - VDIFF(Min)/2
3	Differential input voltage range	V <sub>DIFF(range)</sub>	0.13	0.35	0.49	±V	Same as voltage swing
4	Differential input voltage peak to peak swing	V <sub>DIFF(p-p)</sub>	0.26	0.7	0.98	V <sub>pp</sub>	Differential peak-to-peak absolute voltage swing
5	Input voltage common mode range	VIHCMR	0.84	1.2	1.56	V	
6	High-level input current	I <sub>IH</sub>	_		5.8	mA	
7	Low-level input current	I⊫	_	_	5.8	mA	
8	Input rise/fall time	$t_r$ , $t_f$	_	_	600	ps	20% to 80% of V <sub>DIFF</sub>
	Input clock frequency (Tx)	fclk	_	-	100	MHz	CLKP/CLKN, SCLKP/SCLKN
9	Innert alask francisco (CDI)	£	_	_	100	MHz	SCLKP/SCLKN (Write mode)
	Input clock frequency (SPI)	fsclk	_	_	50	MHz	SCLKP/SCLKN (Read mode)
10	Class duta avala	Dclk	48	50	52	%	CLKP/CLKN
10	Clock duty cycle	Dsclk	45	50	55	%	SCLKP/SCLKN
11	CS setup time	tsu_cs	2.5	-	_	ns	CS to SCLK rise
12	CS hold time	t <sub>HLD_CS</sub>	2.5	-	_	ns	CS to SCLK rise
			1043 T <sub>SCLK</sub>	_	_	ns	Data write to memory
			1050 T <sub>SCLK</sub>	_	_	ns	Data read from memory
			91 Tsclk	_	_	ns	Data write to 9Byte register
13	CS width	tw_cs	108 Tsclk	_	_	ns	Data read from 9Byte register
			243 T <sub>SCLK</sub>	-	_	ns	Data write to 28Byte register
			250 Tsclk	_	_	ns	Data read from 28Byte register
			26 T <sub>SCLK</sub>	_	_	ns	Data read of other register
14	SDATA setup time	tsu_sdata	2.5	-	_	ns	SDATA to SCLK rise
15	SDATA hold time	thld_sdata	2.5	_	_	ns	SDATA to SCLK rise

Remark: External termination Resister ( $100\Omega$ ) is necessary for LVDS I/F differential inputs.

#### 2.2 CMOS logic inputs & outputs

Table 4 CLKP/CLKN, CSP/CSN, SCLKP/SCLKN, SDATAP/SDATAN \*3 EN, CLKIF, TRIG, SPIEN, SDOUT

No.	Items	Symbol	Min.	Тур.	Max.	Units	Condition
1	High-level logic input voltage	V <sub>IH</sub>	$0.8V_{LL}$	ı	V <sub>LL</sub>	<b>V</b>	
2	Low-level logic input voltage	VIL	0	ı	0.2V <sub>LL</sub>	V	
3	Logic input capacitance	Cin	ı	3	_	pF	
4	Logic input high current *1	Iн	-10	ı	10	μΑ	
5	Logic input low current *2	lıL	-10	ı	10	μΑ	
6	Input rise/fall time	tr, tf	ı	ı	2.0	ns	10% to 90% of signal
7	TDIC fall to clock rice actual time	4	1.5	-	_	20	LVDS clock
/	TRIG fall to clock rise setup time	ISU_TRFTOCKR	1.5	ı	_	ns	CMOS clock
	TDIC fall to alook rise hold time	4	1.5	-	_	20	LVDS clock
8	TRIG fall to clock rise hold time	thld_trftockr	1.5	ı	_	ns	CMOS clock
9	TRIG width	tw_trig	3T <sub>CLK</sub>	ı	_	ns	
10	High-level logic output voltage	Vон	$0.8V_{LL}$	I	V <sub>LL</sub>	>	SDOUT
11	Low-level logic output voltage	Vol	0	I	0.2V <sub>LL</sub>	>	SDOUT
12	Logic output off leak current	Ioffleak	-10	I	10	μΑ	SDOUT Hi-Z output
			8	12	18	ns	V <sub>LL</sub> = 1.8V, 10pF load
13	SDOUT Propagation delay	t <sub>D_SDOUT</sub>	7	11	17	ns	V <sub>LL</sub> = 2.5V, 10pF load
	, ,		6	10	16	ns	V <sub>LL</sub> = 3.3V, 10pF load

<sup>\*1.</sup> CLKIF has 50 $\mu$ A leakage at V<sub>LL</sub> = 2.5V due to 50k $\Omega$  internal pull-down resistor.

### 2.3 Open drain output

Table 5 FAULT

No.	Items	Symbol	Min.	Тур.	Max.	Units	Condition
1	Pull-up voltage	$V_{PUFAULT}$	ı	ı	$V_{LL}$	V	Connected to V <sub>LL</sub> with R1
2	Output low voltage	Volfault	ı	ı	0.5	V	Active, $V_{LL} = 2.5V$ , $R1 = 2.5k\Omega$
3	Output current	<b>I</b> FAULT	ı	1.0	ı	mA	V <sub>LL</sub> = 2.5V, R1 = 2.5kΩ
4	Off leak current	Ioffleak	-10	_	10	μΑ	Disabled (Hi-Z)

<sup>\*2.</sup> EN, SPIEN has  $50\mu$ A leakage at  $V_{LL}$  = 2.5V due to  $50k\Omega$  internal pull-up resistor.

<sup>\*3.</sup> Differential CMOS or Single-ended CMOS is also available for CLKP/N, CSP/N, SCLKP/N and SDATAP/N. In case of single-ended CMOS, N-terminals (CLKN, CSPN, SCLKN and SDATAN) need to be connected to half of V<sub>LL</sub> (V<sub>LL</sub>/2).

### 2.4 Logic inputs timing chart

### 2.4.1 LVDS clock inputs

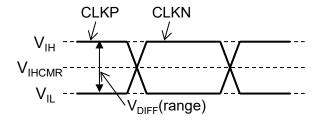


Figure 2 Differential Input Voltage Range (VDIFF(range))

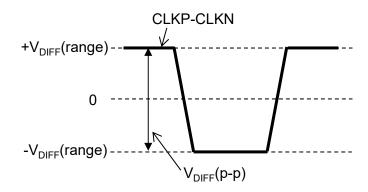


Figure 3 Differential Input Voltage Peak to Peak Swing (VDIFF(p-p))

### 2.4.2 TRIG and setup/hold time

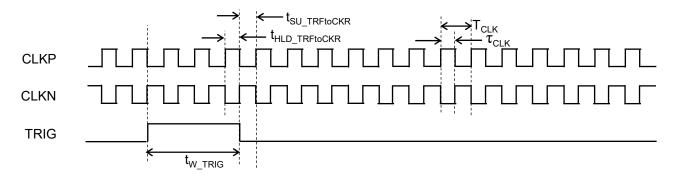


Figure 4

### 2.4.3 SPI inputs and setup/hold time

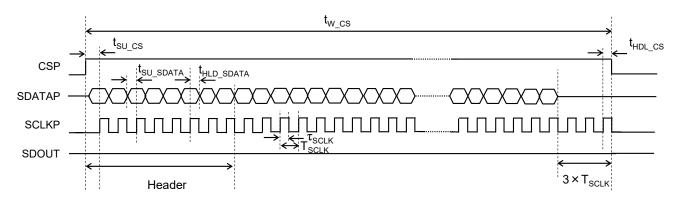


Figure 5 Write Data to Waveform Memory or Registers

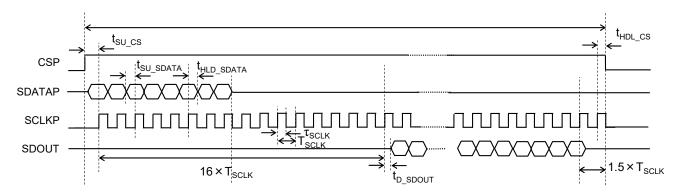


Figure 6 Read Data from Waveform Memory or Registers

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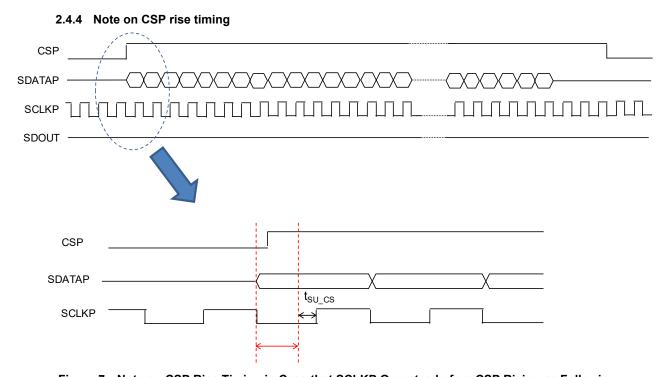


Figure 7 Note on CSP Rise Timing in Case that SCLKP Operates before CSP Rising as Following
In case that SCLKP operates before CSP rising, CSP has to rise during SCLKP is "low" except for setup time "tsu\_cs".

# **■** Typical Application Circuit

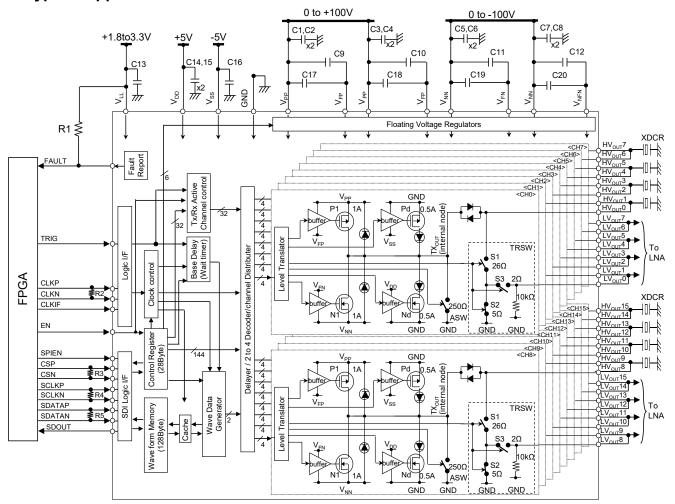


Figure 8 Typical Application Circuit

Remark C1 to C8: Ceramic capacitors of ≥200V 0.1µF to 1µF

C9 to C12: Ceramic capacitors of ≥16V 10µF C13 to C20: Ceramic capacitors of ≥16V 0.1µF

R1: 2.5kΩ

R2 to R5:  $100\Omega$  (for LVDS)

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# **■** Electrical Characteristics

# 1. Operating supply currents

# Table 6 Operating Supply Currents (1/2)

 $V_{LL} = 2.5V, \ V_{DD}/V_{SS} = \pm 5V, \ T_A = 25^{\circ}C, \ CLKP/CLKN = 100MHz, \ HV_{OUT} \ load = 80pF//100\Omega, \ LV_{OUT} \ load = 200pF//300\Omega, \ unless \ otherwise \ specified.$ 

No		Itomo	Cumbal		Spec		Units	Conditions	
No.		Items	Symbol	Min.	Тур.	Max.	Units	Conditions	
	\	SPIEN = H		-	0.05	_	mA		
1	V <sub>LL</sub> current	SPIEN = L	Illad	-	0.10	ı	mA		
2	\/ aat	SPIEN = H		-	6	ı	mA	Quiescent current-1	
2	V <sub>DD</sub> current	SPIEN = L	IDDQD	_	14	_	mA	EN = 1 (Disable)	
3	Vss current		Issqd	_	1.0	_	mA	Current mode 1 (CC = '1') $V_{PP}/V_{NN} = \pm 100V$	
4	V <sub>PP</sub> current		IPPQD	_	0.1	_	mA	VPP/VNN - ±100V	
5	V <sub>NN</sub> current		I <sub>NNQD</sub>	_	0.1	_	mA		
6	V∟∟ current	SPIEN = H	1	_	0.10	_	mA		
0	VLL current	SPIEN = L	ILLQE	_	0.15	_	mA		
		SPIEN = H, CLKIF = H (CMOS)		_	9	_	mA		
		SPIEN = H, CLKIF = L (LVDS)		_	11	_	mA	Quiescent current-2	
7	V <sub>DD</sub> current	SPIEN = L, CLKIF = H (CMOS)	IDDQE	_	16	-	mA	EN = 0 (Enable) Current mode 1 (CC = '1') V <sub>PP</sub> /V <sub>NN</sub> = ±100V	
		SPIEN = L, CLKIF = L (LVDS)		_	18	_	mA	VPP/VNN - ±100V	
8	Vss current		Issqe	_	1.0	_	mA		
9	V <sub>PP</sub> current		I <sub>PPQE</sub>	-	0.3	_	mA		
10	V <sub>NN</sub> current		INNQE	_	0.3	_	mA		
11	V <sub>LL</sub> current	SPIEN = H	ILLPW	-	0.10	_	mA		
'''	VII Current	SPIEN = L	ILLPW	-	0.15	_	mA		
		SPIEN = H, CLKIF = H (CMOS)		_	10	_	mA	PW operating current	
40	\/	SPIEN = H, CLKIF = L (LVDS)		-	13	-	mA	EN = 0 Current mode 1 (CC = '1')	
12	V <sub>DD</sub> current	SPIEN = L, CLKIF = H (CMOS)	Iddpw	_	18	ı	mA	16-channel active Bipolar 3-level 2-cycle	
		SPIEN = L, CLKIF = L (LVDS)		-	21		mA	$f = 5MHz$ , PRT = 200 $\mu$ s $V_{PP}/V_{NN} = \pm 60V$	
13	Vss current		Isspw	-	2	ı	mA		
14	V <sub>PP</sub> current		I <sub>PPPW</sub>	-	8	_	mA		
15	V <sub>NN</sub> current		I <sub>NNPW</sub>	_	9	_	mA		

### Table 6 Operating Supply Currents (2/2)

 $V_{LL} = 2.5V, V_{DD}/V_{SS} = \pm 5V, T_A = 25^{\circ}C, CLKP/CLKN = 100MHz, HV_{OUT} \ load = 80pF//100\Omega, LV_{OUT} \ load = 200pF//300\Omega \ unless otherwise specified.$ 

NI-		14	0		Spec		Units	0	
No.		Items	Symbol	Min.	Тур.	Max.	Units	Conditions	
40	\/	SPIEN = H		-	0.1	-	mA		
16	V <sub>LL</sub> current	SPIEN = L	ILLCW3	-	0.15	ı	mA		
		SPIEN = H, CLKIF = H(CMOS)		_	181	I	mA	CW operating current-1	
47		SPIEN = H, CLKIF = L(LVDS)		-	185	-	mA	EN = 0, CKDIV[1:0] = 10 Current mode 3 (CC='1')	
17	V <sub>DD</sub> current	SPIEN = L, CLKIF = H(CMOS)	Іррсмз	_	189	-	mA	16-channel active Bipolar 3-level Continuous	
		SPIEN = L, CLKIF = L(LVDS)		_	193	-	mA	f = 5MHz $V_{PP}/V_{NN} = \pm 5V$	
18	Vss current		Isscw3	_	34	_	mA		
19	V <sub>PP</sub> current		IPPCW3	_	360	_	mA		
20	V <sub>NN</sub> current		IPPCW3	_	380	_	mA		
04	\/	SPIEN = H		_	0.1	_	mA		
21	V <sub>LL</sub> current	SPIEN = L	ILLCW2	-	0.15	1	mA		
		SPIEN = H, CLKIF = H(CMOS)		-	171	-	mA	CW operating current-2	
22	V <sub>DD</sub> current	SPIEN = H, CLKIF = L(LVDS)		_	175	-	mA	EN = 0, CKDIV[1:0] = 10 Current mode 2 (CC='0')	
22	VDD Current	SPIEN = L, CLKIF = H(CMOS)	IDDCW2	-	179	_	mA	16-channel active Bipolar 3-level Continuous	
		SPIEN = L, CLKIF = L(LVDS)		_	183	_	mA	f = 5MHz Vpp/Vnn = ±5V	
23	Vss current	. ,	Isscw <sub>2</sub>	_	26	_	mA		
24	V <sub>PP</sub> current		IPPCW2	_	310	-	mA		
25	V <sub>NN</sub> current		I <sub>NNCW2</sub>	_	330	_	mA		

#### 2. Static characteristics

#### **Table 7 Static Characteristics**

 $V_{LL}$  = 2.5V,  $V_{DD}/V_{SS}$  = ±5V,  $T_A$  = 25°C, VFP[2:0] = 000, VFN[2:0] = 000, DRVPADJ = 0, DRVNADJ = 0, unless otherwise specified.

No.	Items	Symbol		Spec		Units	Condition
INO.	nems	Symbol	Min.	Тур.	Max.	Ullis	Condition
1	HV <sub>O∪T</sub> x output voltage range	HV <sub>OUT</sub> x	-100	_	+100	V	
2	HV <sub>о∪т</sub> х high-side peak current	Іон	_	1.0	_	А	V <sub>PP</sub> /V <sub>NN</sub> = ±60V, Current mode 1 (CC = 1)
	TOVOUTX HIGH-Side peak current	ЮН	_	0.5	_	Α	$V_{PP}/V_{NN} = \pm 60V$ , Current mode 0 (CC = 0)
3	HV <sub>OUT</sub> x high-side GND clamp peak current	Іонсь	_	0.5	-	Α	V <sub>PP</sub> /V <sub>NN</sub> = ±60V
4	LIV.	1	_	1.0	_	Α	V <sub>PP</sub> /V <sub>NN</sub> = ±60V, Current mode 1 (CC = 1)
4	HV <sub>OUT</sub> x low-side peak current	loL	_	0.5	_	Α	$V_{PP}/V_{NN} = \pm 60V$ , Current mode 0 (CC = 0)
5	HV <sub>OUT</sub> x low-side GND clamp peak current	lolcl	_	0.5	_	Α	V <sub>PP</sub> /V <sub>NN</sub> = ±60V
6	LIV/	D	_	18	-	Ω	I <sub>OH</sub> = 100mA, Current mode 1 (CC = 1)
0	HV <sub>OUT</sub> x high-side on-resistance	Ronh	_	31	-	Ω	I <sub>OH</sub> = 100mA, Current mode 0 (CC = 0)
7	HV <sub>OUT</sub> x high-side GND clamp on-resistance	Ronhcl	_	34	_	Ω	I <sub>OHCL</sub> = 100mA
8	HVолтх low-side on-resistance	D	_	17	_	Ω	I <sub>OL</sub> = 100mA, Current mode 1 (CC = 1)
0	ITVOUTX IOW-SIDE OIT-TESISTANCE	Ronl	_	30	_	Ω	I <sub>OL</sub> = 100mA, Current mode 0 (CC = 0)
9	HV <sub>OUT</sub> x low-side GND clamp on-resistance	Ronlcl	_	33	_	Ω	I <sub>OLCL</sub> = 100mA
10	HV <sub>O∪⊤</sub> x off-capacitance	CHVOFF	_	17	_	pF	TX <sub>OUT</sub> x = GND, TRSW = off

# 3. Dynamic characteristics

## **Table 8 Dynamic Characteristics**

 $V_{LL} = 2.5 \text{V}, \ V_{DD}/V_{SS} = \pm 5 \text{V}, \ T_A = 25^{\circ}\text{C}, \ CLKP/CLKN = 100MHz, \ VFP[2:0] = VFN[2:0] = '000', \ HV_{OUT} \ load = 80pF//100\Omega, \ LV_{OUT} \ load = 200pF//300\Omega, \ unless otherwise specified.$ 

Nia	lta ma	Courada ad		Spec		l linita	Condition
No.	Items	Symbol	Min.	Тур.	Max.	Units	Condition
1	Output frequency	f <sub>OUT</sub>	_	20	ı	MHz	
2	Output rise propagation delay	t <sub>dr</sub>	_	40	-	ns	
3	Output fall propagation delay	t <sub>df</sub>	_	40	ı	ns	
4	Output rise propagation delay clamp	$t_{\sf drCL}$	_	40	_	ns	
5	Output fall propagation delay clamp	t <sub>dfCL</sub>	_	40	-	ns	
6	Propagation delay matching	$\Delta t_{\text{d}}$	_	±1	±3	ns	
			_	13	_	ns	CC = 1
7	Output rise time	t <sub>r</sub>	_	21	-	ns	CC = 0
		t <sub>rCL</sub>	_	9	1	ns	
		+.	_	13	ı	ns	CC = 1
8	Output fall time	t <sub>f</sub>	_	21	-	ns	CC = 0
		t <sub>fCL</sub>	_	9	ı	ns	
9	2nd harmonic distortion	HD2	_	-40	ı	dBc	
10	Pulse cancellation	HDPC	_	-40	-	dBc	Bipolar, 2-сус, fouт = 5МHz
10	Fuse cancellation	HDPC2	_	-40	ı	dBc	
11	RMS output jitter	tJ	_	10	-	ps	Bipolar CW, f <sub>OUT</sub> = 5MHz, V <sub>PP</sub> /V <sub>NN</sub> = ±5V
12	Crosstalk between channels	XTLK	_	-70	_	dB	$f_{OUT} = 5MHz$ , $10V_{p-p}$ , $HV_{OUT}$ load = $50\Omega$

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### 4. Integrated Peripheral Circuits Characteristics

#### 4. 1 T/R Switch characteristics

#### Table 9 T/R Switch Characteristics

 $V_{LL} = 2.5V$ ,  $V_{DD}/V_{SS} = \pm 5V$ ,  $V_{PP}/V_{NN} = \pm 60V$ ,  $T_A = 25^{\circ}C$ , unless otherwise specified.

No.	Items	Cymhol		Spec		Units	Condition
NO.	iterns	Symbol	Min.	Тур.	Max.	Ullis	Condition
1	LV <sub>o∪⊤</sub> x output voltage range	LV <sub>OUT</sub> X	-0.85	ı	+0.85	V	
2	TRSW on-resistance	Rontr	ı	28	ı	Ω	HV <sub>OUT</sub> x = 100mV, LV <sub>OUT</sub> x = 0V
3	TRSW on-capacitance	Contr	ı	7	ı	pF	LV <sub>OUT</sub> X = 0V
4	TRSW off-resistance on HVOUTx	Rofftrhv	1	ĺ	ı	МΩ	
5	TRSW off-resistance on LVOUTx	Rofftrlv	8	10	12	kΩ	
6	Spike voltage on HV <sub>OUT</sub> X and LV <sub>OUT</sub> X	V <sub>TRN</sub>	ı	ı	110	$mV_{PP}$	80pF//100 $\Omega$ load on HV <sub>OUT</sub> X 200pF//300 $\Omega$ load on LV <sub>OUT</sub> X
7	TRSW turn-on time	t <sub>dTRON</sub>	_	300	_	ns	Logic input-to-ready for Rx signal See Fig.15
8	TRSW turn-off time	t <sub>dTROFF</sub>	_	50	100	ns	See Fig.15

#### 4. 2 Analog Switch

#### Table 10 Analog Switch Characteristics

 $V_{LL} = 2.5V$ ,  $V_{DD}/V_{SS} = \pm 5V$ ,  $T_A = 25$ °C, unless otherwise specified.

N	اما	Itomo	Cumbal	,	Spec		Linita	Condition
IN	No.	Items	Symbol	Min.	Тур.	Max.	Units	Condition
,	1	ASW on-resistance	Ronasw	1	250	_	Ω	

### 4.3 HV Blocking Diode

### Table 11 HV Blocking Diode Characteristics

 $V_{LL}$  = 2.5V,  $V_{DD}/V_{SS}$  = ±5V,  $T_A$  = 25°C, unless otherwise specified.

	_	2.0 V, V DD/ V 33 20 V, TA 20 O, UIII						
	اما	Items	Svmbol		Spec		Units	Condition
IN	No.	items	Syllibol	Min.	Тур.	Max.	Ullits	Condition
	1	Forward voltage	.,	ı	1.0	ı	V	I <sub>F</sub> = 100mA
	1	Forward voltage	V <sub>FHVD</sub>	1	1.2	1	V	I <sub>F</sub> = 200mA
	2	Reverse voltage	V <sub>RHVD</sub>	200	1	1	V	$I_R = 1\mu A$

#### 4. 4 LV Noise-cut Diode

#### Table 12 LV Noise-cut Diode Characteristics

 $V_{LL}$  = 2.5V,  $V_{DD}/V_{SS}$  = ±5V,  $T_A$  = 25°C, unless otherwise specified.

No.	Items	Symbol		Spec		Units	Condition
INO.	iteriis	Syllibol	Min.	Тур.	Max.	Ullis	Condition
4	Convert voltage	\/	_	1.1	-	V	I <sub>F</sub> = 100mA
	Forward voltage	VFLVD	1	1.25	1	V	I <sub>F</sub> = 200mA

#### 4. 5 Thermal Protection

### **Table 13 Thermal Protection Characteristics**

 $V_{LL}$  = 2.5V,  $V_{DD}/V_{SS}$  = ±5V,  $T_A$  = 25°C, unless otherwise specified.

No.	Itama	Cumbal		Spec		Units	Condition
NO.	Items	Symbol	Min.	Тур.	Max.	Units	Condition
			90	110	120		THPCTL[1:0] = 00
		T <sub>THP</sub>	120	130	140	°C	THPCTL[1:0] = 01
'	THP temperature threshold		140	150	160	٦.	THPCTL[1:0] = 10
			120	130	140		THPCTL[1:0] = 11 (THP is disabled.)
2	THP reset hysteresis	THYSTHP	5	10	20	°C	

# ■ Operation Mode

Table 14 Operation Mode

Section	EN	CSP	SPIEN*1	TRIG	Tx-PT(x)*2	SPI LVDS Receiver	Memory Write	Memory Read	Register Write	Register Read	Тх	Rx	Operation Mode	
Α	1	0	0	×	×	Bias on							IC disabled	
	•	U	1		•	Bias off			_				TO disabled	
			0			Bias on	<b>\</b>	<b>\</b>	_	✓			IC disabled,	
В	1	1	1	×	×	Bias off	ĺ	ĺ	_	_	-	ı	W/R of Memory and Read of Register	
			0			Bias on	<b>\</b>	<b>\</b>	✓	✓			Rx, W/R of Memory or	
С	0	1	1	×	×	Bias off	1	-	_	_	-	<b>√</b> *3	Register, Reset of Tx Operation	
D	0	0	0	1	×	Bias on						<b>√</b> *3	Rx & Reset of Tx	
U	U	U	1	I	*	Bias off	ı	ı	_	_	_	<b>&gt;</b>	Operation	
Е	0	0	0	0	Concreted	Bias on					√*3	ı	Tx	
	U	U	1	U	Generated	Bias off	ı	ı	_	_	<b>V</b> •	ı	TX	
	0	0	0	0	nono	Bias on						√*3	Dv	
-	F 0 0 -		1	U	none	Bias off	_	_	_	_	_	<b>v</b> -	Rx	

<sup>\*1.</sup> SPIEN Signal is used to reduce the bias current of SPI LVDS Receiver when SPI is not used. (Power on/off time of LVDS receiver is <300ns/<100ns.)</p>

Remark ✓: Available

-: Not available

×: Don't care

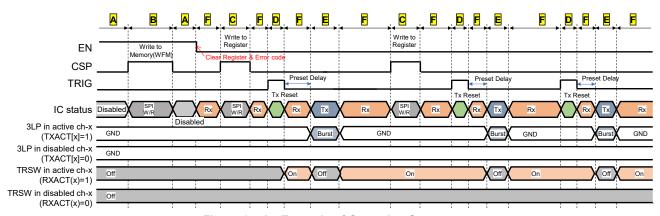


Figure 9 An Example of Operating Sequence

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<sup>\*2.</sup> Tx-PT(x): Tx pattern signal of ch(x)

<sup>\*3.</sup> Individual register parameter on Tx/Rx active channel (TXACT[x] and RXACT[x]) is necessary to be set "1".

# ■ SPI Header Configuration

Table 15 SPI Operation

S	DATA (	Control	Header	· (First 1	1Byte o	f SDAT	A)	SPI operation				
D7 (MSB)	D6	D5	D4	D3	D2	D1	D0 (LSB)	or roperation				
0	0	0	0					Write to the first 9Byte (R#0 to R#8) Control Registers and CRC[7:0]				
0	1	0	0					Write to all 28Byte Control Registers and CRC[7:0]				
1	0	0	0					N/A				
1	1	0	0					Write to Memory and CRC[7:0]				
0	0	0	1			000		Read from the first 9Byte (R#0 to R#8) Control Registers and CRC[7:0]				
0	1	0	1		(Res	erved)		Read from all 28Byte Control Registers and CRC[7:0]				
1	0	0	1					N/A				
1	1	0	1					Read from Memory and CRC[7:0] through SDOUT pin				
×	×	1	0				Read from ERROR[7:0] through SDOUT pin					
×	×	1	1					Read from DSUM[7:0] through SDOUT pin				

<sup>&</sup>lt; 8bit CRC Conditions>

CRC initial value = 00000000 CRC Polynomial equation is  $X^8+X^5+X^4+1$ 

Remark x: Don't care

## ■ Access to Memory or Registers with SPI

### 1. SPI write to memory or registers operation

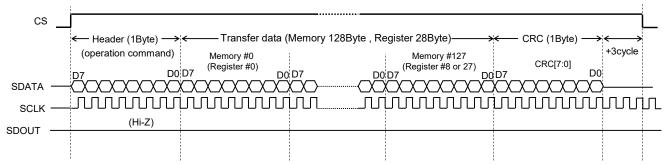


Figure 10 Sequence of Writing to Memory or Registers with SPI

Remark < CRC Conditions>

CRC initial value = 00000000

CRC Polynomial equation is X8+X5+X4+1

In SPI "WRITE" operation, internal logic circuit also calculates the CRC ,and writes it to internal Register DSUM[7:0]. If CRC[7:0] matches DSUM[7:0], ERROR[0] = 0. If unmatched, ERROR[0] = 1 and FAULT pin reports, unless fault report is released.

#### 2. Read back form memory or registers operation

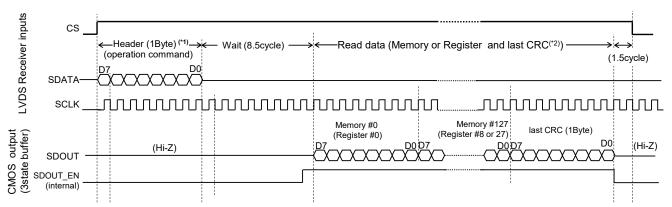


Figure 11 Sequence of Reading from Memory or Registers with SPI

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- \*1. In case of "READ" operation, SDATA inputs except for Header are ignored (CRC error detection is disabled).
- \*2. Last CRC is the received CRC data from FPGA in previous "WRITE" operation to Memory or Register.

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# ■ 3LP+TRSW Operation Example

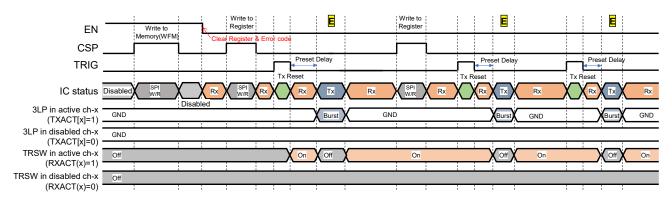


Figure 12 An Example of IC State Timing Diagram and 3LP Operation

Tx starts from TRIG fall edge with preset delay time.
TRSW turns on except for Tx Burst period or IC-disabled.

#### **Generating Tx WF Pattern**

CODE\_[1:0] = output state ( $\pm$ HV, GND) see **Truth Table** Pulse width =  $5ns\times(W_{[5:0]}+2)$  (decimal, 10ns to 325ns) START [6:0] = starting address STOP [6:0] = stopping address Repeat count(s) = 1, 1×REPEAT[7:0], 1×REPEAT[7:0], CW CW mode ends with CS = 1 or TRIG = 1.

# Generating Tx Delay (16ch)

CHx delay time from TRIG fall edge = BASE-DELAY + CHx-DELAY BASE-DELAY(common) = 160ns×(BASEDL[7:0]) + 200ns (decimal, 0.2µs to 41µs)

 $CHx-DELAY(/ch) = 5ns \times (CHxDL[8:0])$ 

 $(x = 0 \text{ to } 15, \text{ decimal}, 0 \text{ to } 2.55 \mu \text{s})$ 

Delay time resolution = 5ns

WFM	M#	Item	D7	D6	D5	D4	D	3	D2	D1	D0
	_	Pulse #0	CODE0	CODE0	W0	W0	W	0	W0	W0	W0
START[6:0]→	0	Puise #0	[1]	[0]	[5]	[4]	[3	3]	[2]	[1]	[0]
£ 2-		D. I	CODE1	CODE1	W1	W1	W	1	W1	W1	W1
	1	Pulse #1	[1]	[0]	[5]	[4]	[3	31	[2]	[1]	[0]
	0	Pulse #2	CODE2	CODE2	W2	W2	W	2	W2	W2	W2
$STOP[6:0] \rightarrow$	2	Pulse #2	[1]	[0]	[5]	[4]	[3	3]	[2]	[1]	[0]
•	•		•	•	•	•			•		
				.	.		.	.			
	127	Pulse #127	CODE127	CODE127	W127	W127	W1	27	W127	W127	W127
	12/	Puise #127	[1]	[0]	[5]	[4]	[3	3]	[2]	[1]	[0]
Register	R#	70	D6	D5	D4		D3			D1	D0
register	0	reserved	STARTI61	START[5]	START[4		RTI31	STAR		START[1]	STARTI01
	1 reserved		STOP[6]	STOP[5]	STOP[4]		DP[3]	STOF		STOP[1]	STOP[0]
	2	INV	MUL-RPT	reserved	CC		)IV[1]	CKDI		THPCTLI11	THPCTLIO
	3	REPEAT[7]	REPEATI61	REPEAT[5]	REPEAT[4		EATI31	REPEAT[2] VFN[2] TXACTI101		REPEAT[1]	REPEAT[0]
\/	4	DRVPADJ	VFP[2]	VFP[1]	VFP[0]		NADJ			VFN[1]	VFN[0]
·Υ	5	TXACT[15]	TXACT[14]	TXACT[13]	TXACTI12		CT[11]			TXACT[9]	TXACT[8]
	6	TXACT[7]	TXACT[6]	TXACT[5]	TXACTI4		CTI31	TXAC		TXACT[1]	TXACT[0]
<b>X</b>	7	RXACT[15]	RXACT[14]	RXACT[13]	RXACT[12		CTI111	RXACT		RXACT[9]	RXACT[8]
	8	RXACT[7]	RXACT[6]	RXACT[5]	RXACT[4	1 RXA	СТІЗІ	RXAC	TI21	RXACT[1]	RXACT[0]
	9	BASEDL[7]	BASEDL[6]	BASEDL[5]	BASEDL[4	BASI	EDL[3]	BASED	DL[2]	BASEDL[1]	BASEDL[0]
`	10	CH0DL[8]	CH0DL[7]	CH0DL[6]	CH0DL[5	CHO	DL[4]	CH0D	L[3]	CH0DL[2]	CH0DL[1]
	11	CH0DL[0]	CH1DL[8]	CH1DL[7]	CH1DL[6	CH1	DL[5]	CH1D	L[4]	CH1DL[3]	CH1-DL[2]
	:	: 1	: :	1 :	:		:	:		: 1	:
	26	CH14DL[6]	CH14DL[5]	CH14DL[4]	CH14DLI3	1 CH14	IDLI21	CH14DL[1]		CH14DL[0]	CH15DL[8]
	27	CH15DL[7]	CH15DL[6]	CH15DL[5]	CH15DL[4					CH15DL[1]	CH15DL[0]

# **■** Truth Table

Table 16 Truth Table

	IC statu	IS	Ext	ternal sig	nal	Internal	Control	Register		FM E[1:0]	Control Register		MOSF	CHx ET/ASW		status		CHx Out	tput state
	mode	SPI	EN	cs	TRIG	Tx-PT(x)	CHx_TX	CHx_RX	[1]	[0]	INV	P1	N1	Pd	Nd	250Ω ASW	TRSW	TXOUTx	LVOUTx
Α	IC disabled	no op.	1	0	×	none	×	×	×	×	×	OFF	OFF	ON	ON	ON	OFF	GND	10kΩ
В	ic disabled	Mem. W	1	1	×	none	×	×	×	×	×	OFF	OFF	ON	ON	ON	OFF	GND	10kΩ
		Memory	0	1	×	none	0	0	×	×	×	OFF	OFF	ON	ON	ON	OFF	GND	10kΩ
С	Rx & Tx Reset	W/R	0	1	×	none	0	1	×	×	×	OFF	OFF	ON	ON	ON	ON	GND	HVOUT <sub>x</sub>
	by SPI W/R	or Register	0	1	×	none	1	0	×	×	×	OFF	OFF	ON	ON	ON	OFF	GND	10kΩ
		W/R	0	1	×	none	1	1	×	×	×	OFF	OFF	ON	ON	ON	ON	GND	HVOUT <sub>x</sub>
			0	0	1	none	0	0	×	×	×	OFF	OFF	ON	ON	ON	OFF	GND	10kΩ
D	Rx & Tx Reset	no on	0	0	1	none	0	1	×	×	×	OFF	OFF	ON	ON	ON	ON	GND	HVOUT <sub>x</sub>
l D	By TRIG	no op.	0	0	1	none	1	0	×	×	×	OFF	OFF	ON	ON	ON	OFF	GND	10kΩ
			0	0	1	none	1	1	×	×	×	OFF	OFF	ON	ON	ON	ON	GND	HVOUT <sub>x</sub>
			0	0	0	Gen.	1	×	0	0	×	OFF	OFF	ON	ON	ON	OFF	GND	10kΩ
			0	0	0	Gen.	1	×	0	1	0	ON	OFF	OFF	OFF	OFF	OFF	+HV	10kΩ
E	Tx	no op.	0	0	0	Gen.	1	×	0	1	1	OFF	ON	OFF	OFF	OFF	OFF	-HV	10kΩ
1-	1.	по ор.	0	0	0	Gen.	1	×	1	0	0	OFF	ON	OFF	OFF	OFF	OFF	-HV	10kΩ
			0	0	0	Gen.	1	×	1	0	1	ON	OFF	OFF	OFF	OFF	OFF	+HV	10kΩ
			0	0	0	Gen.	1	×	1	1	×			N	/A			N.	/A
_	Rx	no on	0	0	0	none	×	0	×	×	×	OFF	OFF	ON	ON	ON	OFF	GND	10kΩ
	ΓX	no op.	0	0	0	none	×	1	×	×	×	OFF	OFF	ON	ON	ON	ON	GND	HVOUT <sub>x</sub>

Remark x: Don't care

Table 17

		i abi	e 17			
Current	CC	DRVP	DRVN	IOUT[A]		
mode	CC	ADJ	ADJ	P1	N1	
		0	0	0.5	0.5	
0	0	0	1	0.5	0.6	
	0 1	0	0.6	0.5		
		1	1	0.6	0.6	
		0	0	1	1	
1	4	0	1	1	1.05	
'	1	1	0	1.05	1	
		1	1	1.05	1.05	

Tal	h	ما	1	R

\	/FPCT	L	VPP-VFP
[2]	[1]	[0]	[V]
0	0	0	5
0	0	1	5.15
0	1	0	5.3
0	1	1	5.45
1	0	0	5
1	0	1	4.85
1	1	0	4.7
1	1	1	4.55

#### Table 19

\	/FNCT	L	VFN-VNN
[2]	[1]	[0]	[V]
0	0	0	5
0	0	1	5.15
0	1	0	5.3
0	1	1	5.45
1	0	0	5
1	0	1	4.85
1	1	0	4.7
1	1	1	4.55

Table 20

THF	CTL	THP Threshold	Tx reset	FAULT
[1]	[0]	[degC]	function	Indication
0	0	110	ON	ON
0	1	130	ON	ON
1	0	150	ON	ON
1	1	130	OFF	ON

## **■** Timing Chart

Control Registers START[6:0] = n STOP[6:0] = n+1

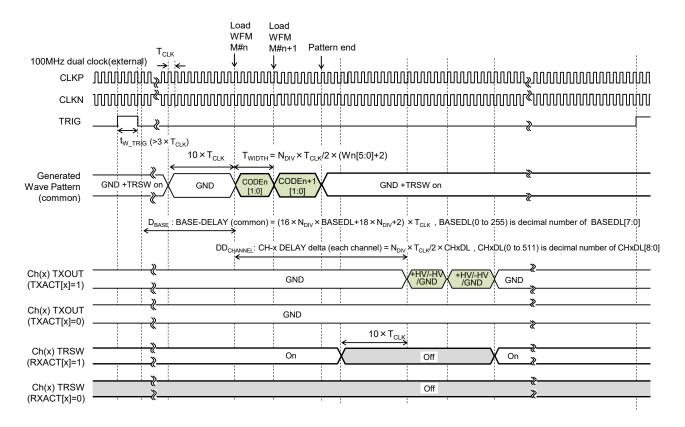


Figure 13 An Example of 3LP State Timing Diagram with Register TXACT[x] & RXACT[x] (x = 0 to 15)

# ■ Tx Burst Timing Chart

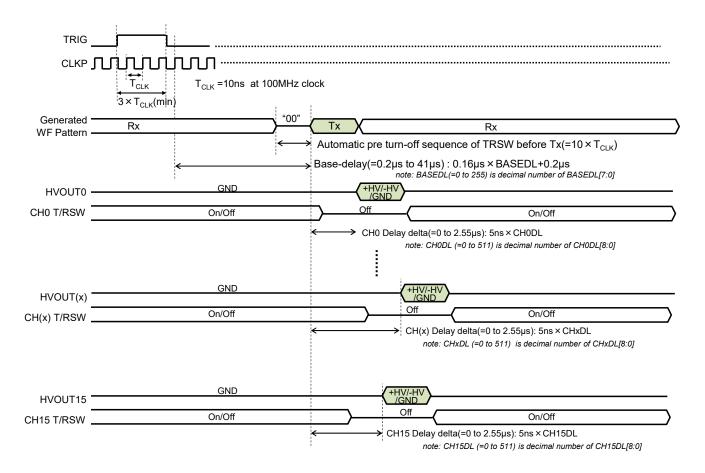


Figure 14 An Example of 3LP State Timing Diagram with Register BASEDL[7:0] & CHxDL[8:0] (x = 0 to 15)

# ■ Tx Propagation Delay and Rise/Fall Time Definition

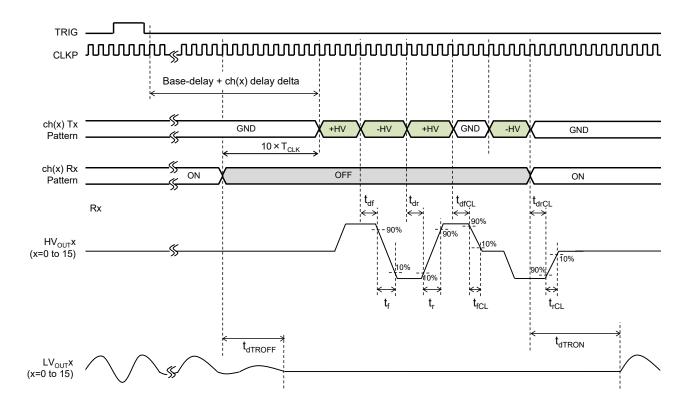


Figure 15 Tx Propagation Delay and Rise/fall Time

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# ■ Tx Pulse Width and Delay Control Table

Table 21 Tx Pulse Width and Delay Control Table

					Spec	;				
No.	Items		Symbol	Min.	Тур.	Max.	Units	Note		
		N <sub>DIV</sub> = 1		10	ı	325		TWIDTH [ns] = NDIV ×TCLK/2 × (WIDTHx + 2)		
1	Tx pulse width	N <sub>DIV</sub> = 2	Twidth	20	1	650	ns	WIDTHx( = 0 to 63) is decimal number of		
		N <sub>DIV</sub> = 4		40	-	1300		WIDTHx[5:0] in memory $\#x$ , $x = 0$ to 127		
	<b>-</b> 1 · 10	N <sub>DIV</sub> = 1		-	5	-				
2	Tx pulse width resolution	N <sub>DIV</sub> = 2	$\Delta T_{WIDTH}$	ı	10	ı	ns	$\Delta T_{WIDTH} = N_{DIV} \times T_{CLK}/2$		
		N <sub>DIV</sub> = 4		1	20	ı				
		N <sub>DIV</sub> = 1		0.2	1	41		D <sub>COM</sub> =(16×N <sub>DIV</sub> ×BASEDL+18×N <sub>DIV</sub> +2)×T <sub>CLK</sub>		
3	Base delay Range	N <sub>DIV</sub> = 2	Осом	0.38	-	81.98	μs	BASEDL( = 0 to 255) is decimal number of		
	Ü		163.94		BASEDL[7:0]					
		N <sub>DIV</sub> = 1		ı	0.16	ı				
4	Base delay resolution	N <sub>DIV</sub> = 2	ΔОсом	ı	0.32	ı	μs	ΔD <sub>COM</sub> = 16×N <sub>DIV</sub> ×T <sub>CLK</sub>		
	resolution	$N_{DIV} = 4$		1	0.64	ı				
	CHx delay	$N_{DIV} = 1$		0	-	2555		DD <sub>CHANNEL</sub> = N <sub>DIV</sub> ×T <sub>CLK</sub> /2×CHxDL		
5	delta range	N <sub>DIV</sub> = 2	DDCHANNEL	0	-	5110	ns	CHxDL( = 0 to 511) is decimal number of CHxDL[8:0]		
	(x = 0  to  15)	N <sub>DIV</sub> = 4		0	ı	10220		x = 0 to 15		
	6 delta resolution	N <sub>DIV</sub> = 1		_	5	_				
6		N <sub>DIV</sub> = 2	ΔDD <sub>CHANNEL</sub>	_	10	-	ns	$\Delta DD_{CHANNEL} = N_{DIV} \times T_{CLK}/2$		
		N <sub>DIV</sub> = 4		_	20	_				

**Remark** N<sub>DIV</sub>( = 1,2,4) is internal clock dividing factor with Register CKDIV[1:0].

CKDIV[1:0] = 00 :  $N_{DIV} = 1$  CKDIV[1:0] = 01 :  $N_{DIV} = 2$  CKDIV[1:0] = 10,11 :  $N_{DIV} = 4$ 

### ■ Memory Map

Table 22 Memory Map

Memory #	D7	D6	D5	D4	D3	D2	D1	D0
0	CODE	0[1:0]		WIDTH0[5:0]				
1	CODE	[1:0]			WIDTI	H1[5:0]		
2	CODE	[2[1:0]			WIDTI	H2[5:0]		
3	CODE3[1:0]		D] WIDTH3[5:0]					
124	CODE124[1:0]				WIDTH	124[5:0]		
125	CODE125[1:0]		WIDTH125[5:0]					
126	CODE126[1:0]		WIDTH126[5:0]					
127	CODE1	27[1:0]			WIDTH	127[5:0]		

- **Remark 1.** In Memory Map, each 1-byte code consists of upper 2-bit CODEx[1:0] and lower 6-bit WIDTHx[5:0]. Suffix "x" corresponds to 1-byte Memory number (x = 0 to 127).
  - 2. CODEx[1:0] stands for an output state of Tx burst as shown in "Truth Table".
  - 3. WIDTHx[5:0] expresses the pulse width  $(T_{WIDTH})$  which is calculated as follows.  $T_{WIDTH} [ns] = N_{DIV} \times T_{CLK}/2 \times (WIDTHx + 2)$
  - **4.** Where, T<sub>CLK</sub> is the CLKP/CLKN clock period, WIDTHx( = 0 to 63) is decimal number of WIDTHx[5:0] and N<sub>DIV</sub>( = 1,2,4) is internal clock dividing factor with Register CKDIV[1:0].
  - **5.** In case of 100MHz CLK,

# ■ Register Parameter Function

Table 23 Register Parameter Function

Table 25 Register Farameter Function				
Items	Register	type	function	
WFM Read Address(start)	START[6:0]	common	Starting address of the Waveform Memory for generating the Tx waveform pattern	
WFM Read Address(stop)	STOP[6:0]	common	Stop address of the Waveform Memory for generating the Tx waveform pattern	
TX Waveform control	INV	common	Inversion control of generating Tx waveform pattern	
Wave generation Repeat control(1)	MUL-RPT	common	Multiplying factor selection for REPEAT[7:0] (1: 1×REPEAT[7:0] , 0: 16×REPEAT[7:0])	
Tx driver current control	СС	common	P1/N1 Tx driver current control (0 = 0.5A, 1 = 1A)	
Tx clock dividing	CKDIV[1:0]	common	Internal clock dividing factor "N <sub>DIV</sub> " selection (00:N <sub>DIV</sub> = 1, 01:N <sub>DIV</sub> = 2, 10 or 11 :N <sub>DIV</sub> = 4)	
P1 Driver adjustment	DRVPADJ	common	n 0: none, 1: Add 0.1A to P1 driver current	
N1 Driver adjustment	DRVNADJ	common	0: none, 1: Add 0.1A to N1 driver current	
Built-in power supply control for P1	VFP[2:0]	common	VFP[2] = 0: VPP1-VFP1 ( = 5 to 5.45) : 5+0.15×VFP, VFP is decimal number of VFP[1:0] VFP[2] = 1: VPP1-VFP1( = 4.55 to 5) : 5-0.15×VFP, VFP is decimal number of VFP[1:0]	
Built-in power supply control for N1	VFN[2:0]	common	VFN[2] = 0: VFN1-VNN1 ( = 5 to 5.45) : 5+0.15×VFN, VFN is decimal number of VFN[1:0]	
THP detection control	THPCTL [1:0]	common	THP detection control (00: 110°C, 01: 130°C, 10: 150°C, 11: Disabled)	
Wave generation Repeat control(2)	REPEAT [7:0]	common	Repeat counts control of Tx waveform pattern generation	
Active channel control for Tx	TXACT [15:0]	/channel	Active channel control in Tx, TXACT[x] corresponds to ch(x) in Tx	
Active channel control for Rx	RXACT [15:0]	/channel	Active channel control of T/R-SW, RXACT[x] corresponds to TRSW of ch(x)	
TX delay control (1)	BASEDL [7:0]	common	Tx offset delay (common to all channel):  (16×N <sub>DIV</sub> ×BASEDL+14×N <sub>DIV</sub> +2)×T <sub>CLK</sub> BASEDL( = 0 to 255) is decimal number of BASEDL[7:0],  T <sub>CLK</sub> is external clock period.	
TX delay control (2)	CHxDL[8:0]	/channel	Tx delay for each channel x (x = 0 to 15) : CHxDL $\times$ NDIV $\times$ TCLK/2 CHxDL( = 0 to 511) is decimal number of CHxDL[8:0] , TCLK is external clock period.	

REPEAT[7:0] (Repeat counts control of Tx waveform pattern generation)

REPEAT[7:0] = 00000000 : repeat count = 1

REPEAT[7:0] = 00000001 to 111111110 : repeat count = 1( or 16)×REPEAT[7:0]

REPEAT[7:0] = 11111111 : continuous

# ■ Tx Control Register MAP

Table 24 Tx Control Register MAP

R#	D7	D6	D5	D4	D3	D2	D1	D0
0	reserved	START[6]	START[5]	START[4]	START[3]	START[2]	START[1]	START[0]
1	reserved	STOP[6]	STOP[5]	STOP[4]	STOP[3]	STOP[2]	STOP[1]	STOP[0]
2	INV	MUL-RPT	reserved	СС	CKDIV[1]	CKDIV[0]	THPCTL[1]	THPCTL[0]
3	REPEAT[7]	REPEAT[6]	REPEAT[5]	REPEAT[4]	REPEAT[3]	REPEAT[2]	REPEAT[1]	REPEAT[0]
4	DRVPADJ	VFP[2]	VFP[1]	VFP[0]	DRVNADJ	VFN[2]	VFN[1]	VFN[0]
5	TXACT[15]	TXACT[14]	TXACT[13]	TXACT[12]	TXACT[11]	TXACT[10]	TXACT[9]	TXACT[8]
6	TXACT[7]	TXACT[6]	TXACT[5]	TXACT[4]	TXACT[3]	TXACT[2]	TXACT[1]	TXACT[0]
7	RXACT[15]	RXACT[14]	RXACT[13]	RXACT[12]	RXACT[11]	RXACT[10]	RXACT[9]	RXACT[8]
8	RXACT[7]	RXACT[6]	RXACT[5]	RXACT[4]	RXACT[3]	RXACT[2]	RXACT[1]	RXACT[0]
9	BASEDL[7]	BASEDL[6]	BASEDL[5]	BASEDL[4]	BASEDL[3]	BASEDL[2]	BASEDL[1]	BASEDL[0]
10	CH0DL[8]	CH0DL[7]	CH0DL[6]	CH0DL[5]	CH0DL[4]	CH0DL[3]	CH0DL[2]	CH0DL[1]
11	CH0DL[0]	CH1DL[8]	CH1DL[7]	CH1DL[6]	CH1DL[5]	CH1DL[4]	CH1DL[3]	CH1-DL[2]
12	CH1DL[1]	CH1DL[0]	CH2DL[8]	CH2DL[7]	CH2DL[6]	CH2DL[5]	CH2DL[4]	CH2DL[3]
13	CH2DL[2]	CH2DL[1]	CH2DL[0]	CH3DL[8]	CH3DL[7]	CH3DL[6]	CH3DL[5]	CH3DL[4]
14	CH3DL[3]	CH3DL[2]	CH3DL[1]	CH3DL[0]	CH4DL[8]	CH4DL[7]	CH4DL[6]	CH4DL[5]
15	CH4DL[4]	CH4DL[3]	CH4DL[2]	CH4DL[1]	CH4DL[0]	CH5DL[8]	CH5DL[7]	CH5DL[6]
16	CH5DL[5]	CH5DL[4]	CH5DL[3]	CH5DL[2]	CH5DL[1]	CH5DL[0]	CH6DL[8]	CH6DL[7]
17	CH6DL[6]	CH6DL[5]	CH6DL[4]	CH6DL[3]	CH6DL[2]	CH6DL[1]	CH6DL[0]	CH7DL[8]
18	CH7DL[7]	CH7DL[6]	CH7DL[5]	CH7DL[4]	CH7DL[3]	CH7DL[2]	CH7DL[1]	CH7DL[0]
19	CH8DL[8]	CH8DL[7]	CH8DL[6]	CH8DL[5]	CH8DL[4]	CH8DL[3]	CH8DL[2]	CH8DL[1]
20	CH8DL[0]	CH9DL[8]	CH9DL[7]	CH9DL[6]	CH9DL[5]	CH9DL[4]	CH9DL[3]	CH9-DL[2]
21	CH9DL[1]	CH9DL[0]	CH10DL[8]	CH10DL[7]	CH10DL[6]	CH10DL[5]	CH10DL[4]	CH10DL[3]
22	CH10DL[2]	CH10DL[1]	CH10DL[0]	CH11DL[8]	CH11DL[7]	CH11DL[6]	CH11DL[5]	CH11DL[4]
23	CH11DL[3]	CH11DL[2]	CH11DL[1]	CH11DL[0]	CH12DL[8]	CH12DL[7]	CH12DL[6]	CH12DL[5]
24	CH12DL[4]	CH12DL[3]	CH12DL[2]	CH12DL[1]	CH12DL[0]	CH13DL[8]	CH13DL[7]	CH13DL[6]
25	CH13DL[5]	CH13DL[4]	CH13DL[3]	CH13DL[2]	CH13DL[1]	CH13DL[0]	CH14DL[8]	CH14DL[7]
26	CH14DL[6]	CH14DL[5]	CH14DL[4]	CH14DL[3]	CH14DL[2]	CH14DL[1]	CH14DL[0]	CH15DL[8]
27	CH15DL[7]	CH15DL[6]	CH15DL[5]	CH15DL[4]	CH15DL[3]	CH15DL[2]	CH15DL[1]	CH15DL[0]

# **■** CRC and Error Register

Table 25 CRC, Calculated CRC and ERROR Register MAP

Register	D7	D6	D5	D4	D3	D2	D1	D0
CRC		CRC[7:0]						
Calculated CRC		DSUM[7:0]						
Error	ERROR[7:0]							

# Table 26 CRC, Calculated CRC and ERROR Register Function

CRC[7:0]	Transferred CRC data in SDATA  CRC initial value = 000000000  CRC Polynomial equation is X <sup>8</sup> +X <sup>5</sup> +X <sup>4</sup> +1			
DSUM[7:0]	Calculated CRC values with transferred SDATA signal			
ERROR[7:0]	When Error has occurred, ERROR register corresponding to error type is set to be "1".  ERROR[7:3]: Not used.  ERROR[2]: threshold over of the junction temperature set in advance.  ERROR[1]: start and stop address for Tx waveform pattern generation are same.  ERROR[0]: SPI transfer error (CRC un-match) has occurred.			

Remark Error[7:0] are cleared when IC is powered on or "EN" becomes from "high" to "low" (fall edge).

# **■** Pin Configuration

Table 27 Pin Configuration (1/2)

Pin#	Pin Name	Function
1	VFN	Built-in power supply for channel 0 to channel 7 N-MOS (N1) gate drive
2	LVOUT1	Low voltage output of channel 1
3	LVOUT0	Low voltage output of channel 0
4	GND	Logic power ground (0V)
5	GND	Logic power ground (0V)
6	EN	Control of chip enable, H = disable, L = enable (50kΩ internal pull-up)
7	FAULT	Fault output flag, open N-MOS drain
8	VDD	Positive low voltage power supply (+5V)
9	CLKP	Positive LVDS clock input (up to 100MHz)
10	CLKN	Negative LVDS clock Input (up to 100MHz)
11	GND	Logic power ground (0V)
12	TRIG	Tx Trigger signal
13	VLL	Positive low voltage power supply (+1.8 to 3.3V)
14	CLKIF	I/F selection of CLKP/CLKN, H: CMOS, L: LVDS (50kΩ internal pull-down)
15	LVOUT15	Low voltage output of channel 15
16	LVOUT14	Low voltage output of channel 14
17	VFN	Built-in power supply for ch8 to ch15 N-MOS (N1) gate drive
18	HVOUT15	High voltage output of channel 15
19	HVOUT14	High voltage output of channel 14
20	VPP	ch8 to ch15 positive high voltage power supply (0 to +100V)
21	HVOUT13	High voltage output of channel 13
22	HVOUT12	High voltage output of channel 12
23	VNN	channel 8 to channel 15 Negative high voltage power supply (0 to -100V)
24	LVOUT13	Low voltage output of channel 13
25	LVOUT13	Low voltage output of channel 12
26	HGND	channel 8 to channel 15 Drive power ground (0V)
27	LVOUT11	Low voltage output of channel 11
28	LVOUT10	Low voltage output of channel 10
29	VNN	channel 8 to channel 15 Negative high voltage power supply (0 to -100V)
30	HVOUT11	High voltage output of channel 11
31	HVOUT10	High voltage output of channel 10
32	VPP	channel 8 to channel 15 positive high voltage power supply (0 to +100V)
33	HVOUT9	High voltage output of channel 9
34	HVOUT8	High voltage output of channel 8
		ů ů i
35 36	VFP LVOUT9	Built-in power supply for channel 0 to channel 7 P-MOS (P1) gate drive  Low voltage output of channel 9
	LVOUT8	
37		Low voltage output of channel 8  SPI serial output data
38	SDOUT SPIEN	Control of SPI Receiver Enable, H = disable, L = enable (50kΩ internal pull-up)
39		1 17
40	SDATAN	SPI positive serial input data (LVDS/CMOS)  SPI negative serial input data (LVDS/CMOS)
41	SDATAN	U I I
42	VDD	Positive low voltage power supply (+5V)
43	GND	Logic power ground (0V)
44	VSS	Negative low voltage power supply (-5V)
45	SCLKP	SPI Positive LVDS/CMOS clock input (up to 100MHz)
46	SCLKN	SPI negative LVDS/CMOS clock Input (up to 100MHz)
47	CSP	SPI positive chip select signal (LVDS/CMOS)
48	CSN	SPI negative chip select signal (LVDS/CMOS)
49	LVOUT7	Low voltage output of channel 7
50	LVOUT6	Low voltage output of channel 6
51	VFP	Built-in power supply for channel 0 to channel 7 P-MOS (P1) gate drive

Table 27 Pin Configuration (2/2)

Pin#	Pin Name	Function
52	HVOUT7	High voltage output of channel 7
53	HVOUT6	High voltage output of channel 6
54	VPP	channel 0 to channel 7 positive high voltage power supply (0 to +100V)
55	HVOUT5	High voltage output of channel 5
56	HVOUT4	High voltage output of channel 4
57	VNN	channel 0 to channel 7 Negative high voltage power supply (0 to -100V)
58	LVOUT5	Low voltage output of channel 5
59	LVOUT4	Low voltage output of channel 4
60	HGND	channel 0 to channel 7 Drive power ground (0V)
61	LVOUT3	Low voltage output of channel 3
62	LVOUT2	Low voltage output of channel 2
63	VNN	channel 0 to channel 7 Negative high voltage power supply (0 to -100V)
64	HVOUT3	High voltage output of channel 3
65	HVOUT2	High voltage output of channel 2
66	VPP	channel 0 to channel 7 positive high voltage power supply (0 to +100V)
67	HVOUT1	High voltage output of channel 1
68	HVOUT0	High voltage output of channel 0

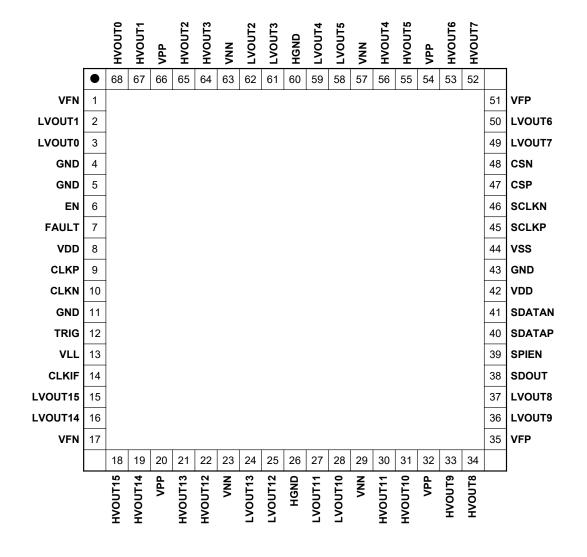


Figure 16 Pin Configuration

# ■ Package

#### **Table28 Package Drawing Codes**

Package Name	Dimension	Tray	Marking	Land	Packing
QFN-68(1010)B	QN068-B-P	QN068-B-T	QN068-B-M	QN068-B-L	QN068-B-K

# ■ Storage, Mounting

#### 1. Storage Conditions

- 1.1 The storage location should be kept at 5 to 35 °C and 40 to 70% relative humidity. Keeping in a dry box is recommended. Moisture-proof property is assured for 12 months from delivery date for sealed moisture-proof packing, while it is guaranteed for 7 days from unpacked date under the condition above.
- 1.2 When the storage conditions do not conform to those above or other conditions occur indicating moisture exposure, the ICs should be dried to avoid package cracks. A baking process at 125 °C lasting for 24 hours results in sufficient dehumidification. The baking is not allowed more than twice, and the ICs should be mounted within 7 days after initial baking or within 10 days of total exposure after the second dehumidification.

#### 2. Reflow soldering

The temperature rise may be different in the resin and a terminal part due to the reflow soldering. It is necessary to check the package surface temperature (resin) before setting the temperature profile. **Figure 17** shows the resistance to soldering heat condition for package (Reflow method). Confirm the heat resistance of the package shown below. (Based on JEDEC J-STD-020).

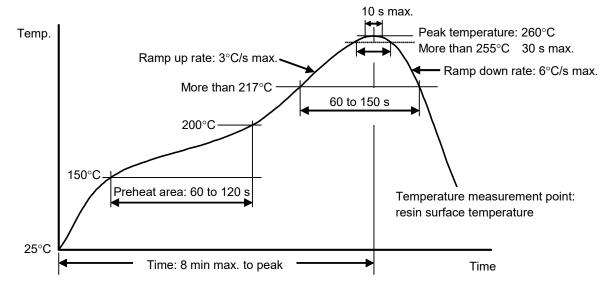


Figure 17 Resistance to Soldering Heat Condition for Package (Reflow Method)

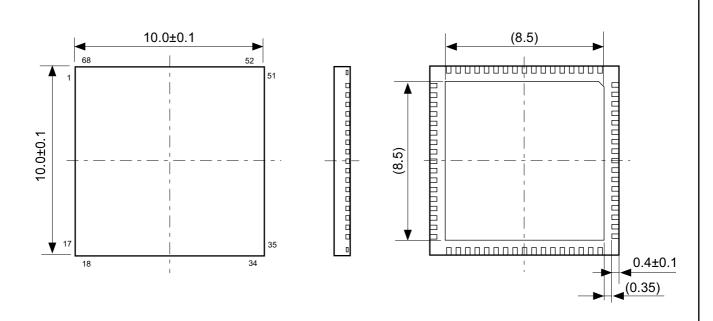
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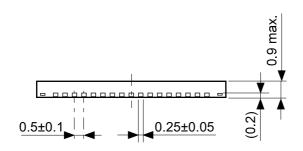
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#### ■ Cautions

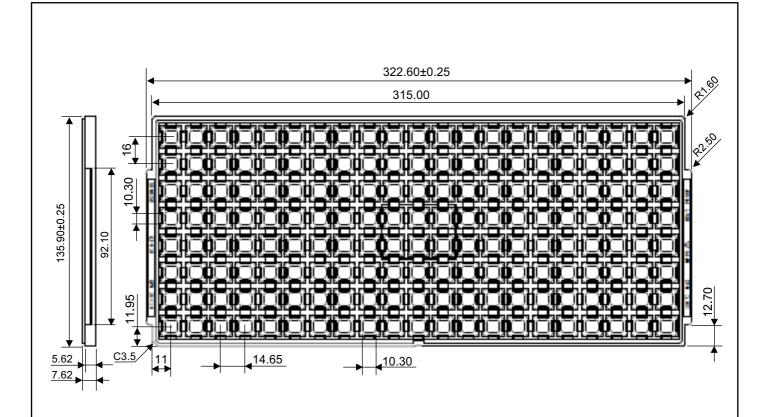
- 1. Customers are advised to follow the cautions below to protect products from damage caused by electrical static discharge (ESD).
  - **1.1** Material of container or any device to carry products should be free from ESD, which may be caused by vibration while transportation. It is recommended that electric-conductive container or aluminum sheet be used as an effective countermeasure.
  - **1.2** Those what touch products such as work platform, machine, measurement/test equipment should be grounded.
  - 1.3 Those who deal with products should be grounded through a large series impedance around  $100k\Omega$  to  $1M\Omega$ .
  - **1.4** Prevent friction with other materials made with high polymer.
  - **1.5** Prevent vibration or friction when carrying the printed circuit board (PCB) where products are mounted. To short circuit terminals is a recommended countermeasure to keep the same electric potential on the PCB.
  - **1.6** Avoid dealing with or storing products in an extremely arid environment.
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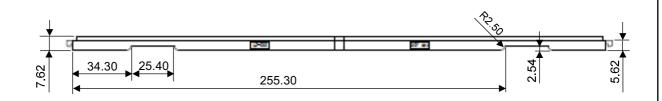


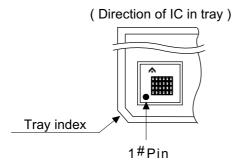


# No. QN068-B-P-SD-1.0

TITLE	QFN68-B-PKG Dimensions	
No.	QN068-B-P-SD-1.0	
ANGLE	<b>\$</b> =3	
UNIT	mm	
ABLIC Inc.		

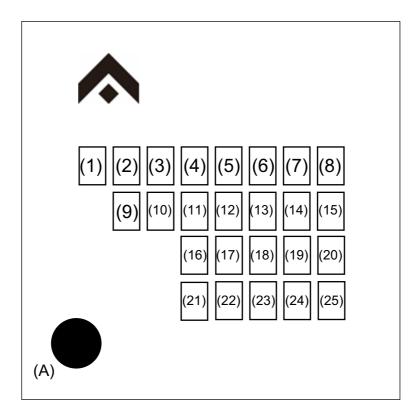






No. QN068-B-T-SD-1.0

TITLE	QFN68-B-Tray			
No.	QN068	QN068-B-T-SD-1.0		
ANGLE		QTY.	168	
UNIT	mm			
	ABLIC Inc.			



(1) to (10) : Product code

(11), (12) : Quality control code

(13) : Year of assembly

(14) : Month of assembly

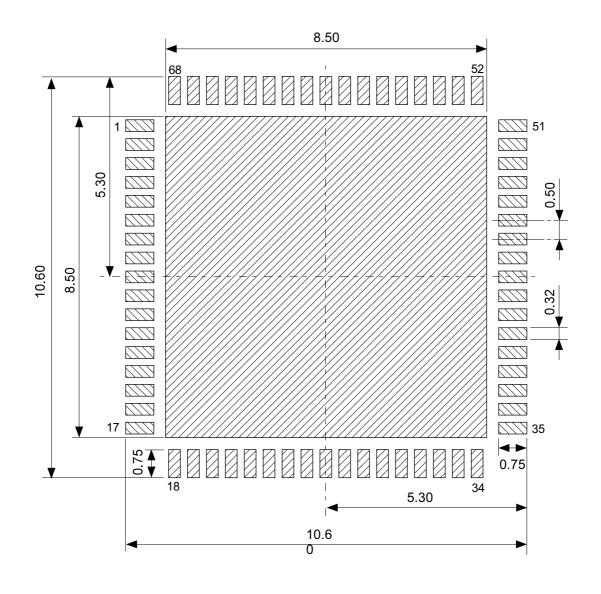
(15) : Week of assembly

(16) to (25): Quality control code

(A) : 1-pin mark

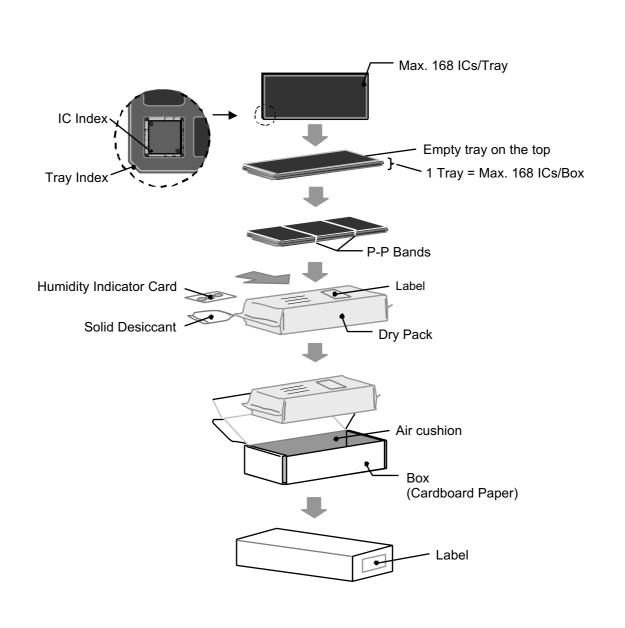
# No. QN068-B-M-S1-1.0

TITLE	QFN68-B-Ma	arkin	gs
No.	QN068-B-M-S1-1.0		
ANGLE			
UNIT	Т.	TYPE	LASER
ABLIC Inc.			



# No. QN068-B-L-SD-1.0

TITLE	QFN68-B -Land Recommendation	
No.	QN068-B-L-SD-1.0	
ANGLE		
UNIT	mm	
ABLIC Inc.		



TITLE	QFN68-B -Packing Procedure
No.	QN068-B-K-SD-2.0
ANGLE	
UNIT	
ABLIC Inc.	

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